

In the Claims

This listing of claims will replace all prior versions, and listings, of claims in the application.

1. (Currently Amended) A method for fabricating a transistor comprising:
 - forming a gate electrode on a semiconductor substrate;
 - forming a first preliminary source/drain region and a pocket junction region through a first ion implantation process using the gate electrode as a mask, the pocket junction region being formed under the first preliminary source/drain region;
 - forming a first oxide layer on the substrate including the gate electrode;
 - forming a nitride layer on the first oxide layer;
 - forming a second oxide layer over the nitride layer;
 - forming spacers on sidewalls of the gate electrode;
 - forming a second preliminary source/drain region through a second ion implantation process using the spacers as a mask;
 - removing the nitride layer and the first oxide layer on the surface of the substrate such that the nitride layer and the first oxide layer remain on the substrate only below the spacers after forming the second preliminary source/drain region through the second ion implantation process using the spacers as a mask; and
 - diffusing substantially all of the implanted ions in a horizontal direction of the substrate by performing a thermal treatment process for the resulting substrate.
2. (Original) The method as defined by claim 1, further comprising performing a thermal treatment process prior to the removal of the nitride layer and the first oxide layer.